



NPN SURFACE MOUNT SMALL SIGNAL TRANSISTOR

Features

- Ideally Suited for Automated Insertion
- **Epitaxial Planar Die Construction**
- For Switching, AF Driver and Amplifier Applications
- Complementary PNP Types Available (BC807)
- Lead, Halogen and Antimony Free, RoHS Compliant
- "Green" Device (Notes 3 and 4)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound, Note 4. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Matte Tin Finish annealed over Alloy 42 leadframe (Lead Free Plating) Solderable per MIL-STD-202, Method 208
- Pin Connections: See Diagram
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.008 grams (approximate)



Device Schematic



Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	45	V
Emitter-Base Voltage	V _{EBO}	5.0	V
Collector Current	I _C	800	mA
Peak Collector Current	I _{CM}	1000	mA
Peak Emitter Current	I _{EM}	1000	mA

Thermal Characteristics

Document number: DS11107 Rev. 18 - 2

Characteristic	Symbol	Value	Unit
Power Dissipation at T _{SB} = 50°C (Note 1)	P_{D}	310	mW
Thermal Resistance, Junction to Substrate Backside (Note 1)	$R_{\theta SB}$	320	°C/W
Thermal Resistance, Junction to Ambient Air (Note 1)	$R_{ hetaJA}$	403	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-65 to +150	°C

Electrical Characteristics @TA = 25°C unless otherwise specified

Characteris	tic (Note 2)	Symbol	Min	Max	Unit	Test Condition
DC Course of Coin	Current Gain Group -16 -25 -40	-	100 160 250	250 400 600	_	V _{CE} = 1.0V, I _C = 100mA
DC Current Gain	Current Gain Group -16 -25 -40	h _{FE}	60 100 170		_	V _{CE} = 1.0V, I _C = 300mA
Collector-Emitter Saturation Vo	$V_{CE(SAT)}$		0.7	V	$I_C = 500 \text{mA}, I_B = 50 \text{mA}$	
Base-Emitter Voltage	V_{BE}	1	1.2	V	$V_{CE} = 1.0V, I_{C} = 300mA$	
Collector-Emitter Cutoff Currer	I _{CES}	1	100 5.0	nΑ μΑ	V _{CE} = 45V V _{CE} = 25V, T _j = 150°C	
Emitter-Base Cutoff Current	I _{EBO}	-	100	nA	V _{EB} = 4.0V	
Gain Bandwidth Product	f⊤	100		MHz	$V_{CE} = 5.0V, I_{C} = 10mA,$ f = 50MHz	
Collector-Base Capacitance		C_{CBO}	_	12	pF	V _{CB} = 10V, f = 1.0MHz

Notes:

- Device mounted on Ceramic Substrate 0.7mm; 2.5cm² area.
- 2. Short duration pulse test used to minimize self-heating effect.
- No purposefully added lead. Halogen and Antimony Free.
 Product manufactured with Data Code V9 (week 33, 2008) and newer are built with Green Molding Compound. Product manufactured prior to Date Code V9 are built with Non-Green Molding Compound and may contain Halogens or Sb₂O₃ Fire Retardants.

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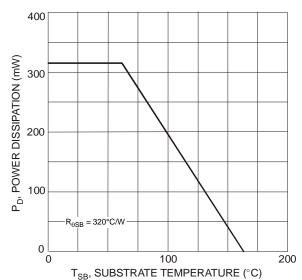


Fig. 1 Power Dissipation vs. Substrate Temperature (Note 1)

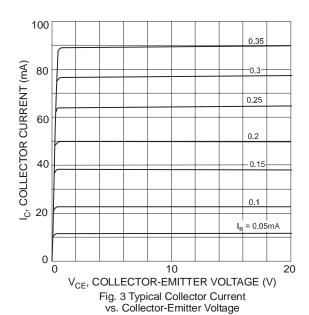


Fig. 5 Typical Collector-Emitter Saturation Voltage vs. Collector Current

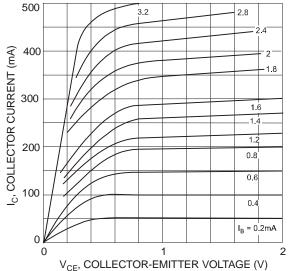


Fig. 2 Typical Collector Current vs. Collector-Emitter Voltage

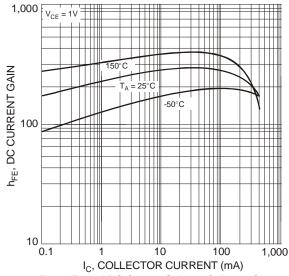


Fig. 4 Typical DC Current Gain vs. Collector Current

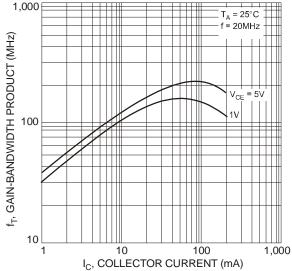


Fig. 6 Gain-Bandwidth Product vs. Collector Current



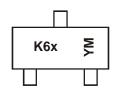
Ordering Information (Note 5)

Part Number	Case	Packaging
BC817-xx-7-F	SOT-23	3000/Tape & Reel

*xx = gain group, e.g. BC817-16-7-F.

Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



K6x = Product Type Marking Code:

K6A = BC817-16

K6B = BC817-25

K6C = BC817-40

YM = Date Code Marking

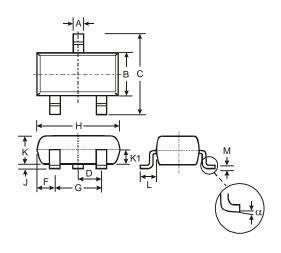
Y = Year (ex: T = 2006)

M = Month (ex: 9 = September)

Date Code Key

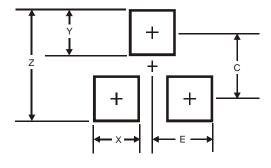
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Package Outline Dimensions



SOT-23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.903	1.10	1.00				
K1	-	-	0.400				
L	0.45	0.61	0.55				
M	0.085	0.18	0.11				
α	0°	8°	-				
All	Dimens	ions in	mm				

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35



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